

INTEGRATED CAPACITIVE AND INDUCTIVE POWER SOURCES FOR A PLASMA ETCHING CHAMBER

ABSTRACT OF THE DISCLOSURE

[54] Broadly speaking, the present invention fills these needs by providing an improved chamber cleaning mechanism. The present invention can also be used to provide additional knobs to tune the etch processes. In one embodiment, a plasma processing chamber configured to generate a plasma includes a bottom electrode assembly with an bottom electrode, wherein the bottom electrode is configured to receive a substrate. The plasma processing chamber includes a top electrode assembly with a top electrode and an inductive coil surrounding the top electrode. The inductive coil is configured to convert a gas into a plasma within a region defined within the chamber, wherein the region is outside an area defined above a top surface of the bottom electrode.

Figure 1A